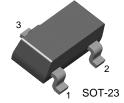


### BC846/847/848/849/850

# Switching and Amplifier Applications - Suitable for automatic insertion in thick and thin-film circuits

- Low Noise: BC849, BC850
- Complement to BC856 ... BC860



1. Base 2. Emitter 3. Collector

### **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage		
020	: BC846	80	V
	: BC847/850	50	V
	: BC848/849	30	V
$V_{CEO}$	Collector-Emitter Voltage		
	: BC846	65	V
	: BC847/850	45	V
	: BC848/849	30	V
$V_{EBO}$	Emitter-Base Voltage		
	: BC846/847	6	V
	: BC848/849/850	5	V
I <sub>C</sub>	Collector Current (DC)	100	mA
I <sub>C</sub> P <sub>C</sub>	Collector Power Dissipation	310	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

### **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}=30V$ , $I_{E}=0$			15	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =5V, I <sub>C</sub> =2mA	110		800	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		90 200	250 600	mV mV
V <sub>BE</sub> (sat)	Collector-Base Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA I <sub>C</sub> =100mA, I <sub>B</sub> =5mA		700 900		mV mV
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ =5V, $I_{C}$ =2mA $V_{CE}$ =5V, $I_{C}$ =10mA	580	660	700 720	mV mV
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=100MHz		300		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		3.5	6	pF
C <sub>ib</sub>	Input Capacitance	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1MHz		9		pF
NF	Noise Figure : BC846/847/848 : BC849/850 : BC849 : BC850	$V_{CE}$ =5V, $I_{C}$ =200 $\mu$ A f=1KHz, $R_{G}$ =2K $\Omega$ $V_{CE}$ =5V, $I_{C}$ =200 $\mu$ A $R_{G}$ =2K $\Omega$ , f=30~15000Hz		2 1.2 1.4 1.4	10 4 4 3	dB dB dB dB

## h<sub>FE</sub> Classification

Classification	А	В	С
h <sub>FE</sub>	110 ~ 220	200 ~ 450	420 ~ 800

## **Marking Code**

Type	846 847			848			849			850					
Type	Α	В	С	Α	В	С	Α	В	С	Α	В	С	Α	В	С
Mark	8AA	8AB	8AC	8BA	8BB	8BC	8CA	8CB	8CC	8DA	8DB	8DC	8EA	8EB	8EC

## **Typical Characteristics**

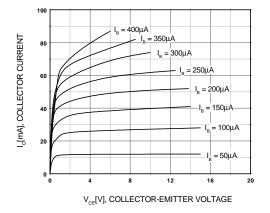


Figure 1. Static Characteristic

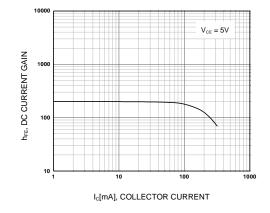


Figure 2. DC current Gain

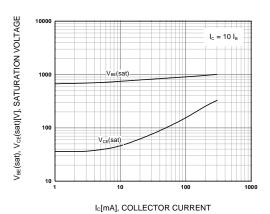


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

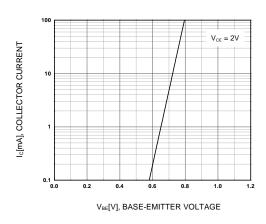


Figure 4. Base-Emitter On Voltage

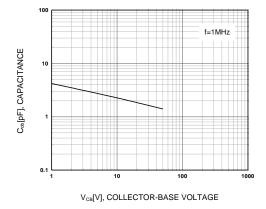


Figure 5. Collector Output Capacitance

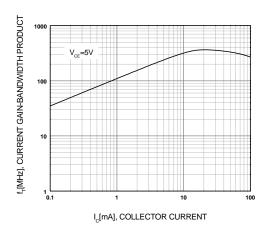
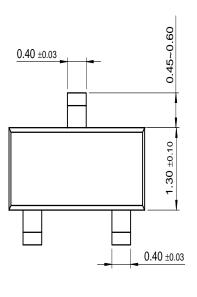


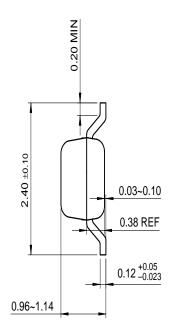
Figure 6. Current Gain Bandwidth Product

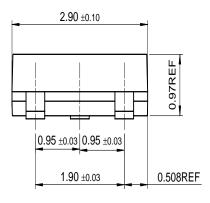
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## **Package Dimensions**

## **SOT-23**







Dimensions in Millimeters

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Bottomless™	FAST <sup>®</sup>	LittleFET™	Power247™	SuperSOT™-3
CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
$CROSSVOLT^{TM}$	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franci	hise™	OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX <sup>TM</sup>
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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